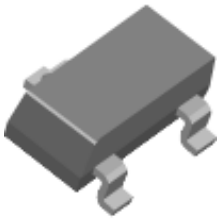
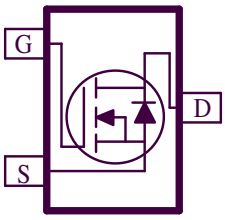
N-Channel 100V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	2 @ V_{GS} = 10 V	0.7
	2.2 @ V_{GS} = 5.5V	0.6

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Maximum**	**Units**
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[a]	T_A=25°C	I_D	0.7	A
Pulsed Drain Current[b]		I_{DM}	±10	
Continuous Source Current (Diode Conduction)[a]		I_S	1.1	A
Power Dissipation[a]	T_A=25°C	P_D	1.30	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typ**	**Max**	
Maximum Junction-to-Ambient[a]	t <= 10 sec	R_{thJA}	93	110	°C/W
	Steady State		130	150	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	1			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V			±10	µA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V			1	µA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55°C			10	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	10			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 0.1 A			2	Ω
		V_{GS} = 5.5 V, I_D = 0.1 A			2	
Forward Tranconductance[A]	g_{fs}	V_{DS} = 10 V, I_D = 0.1 A		11.3		S
Diode Forward Voltage	V_{SD}	I_S = 0.1 A, V_{GS} = 0 V		0.75		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 5.5 V, I_D = 0.1 A		1		nC
Gate-Source Charge	Q_{gs}			0.2		
Gate-Drain Charge	Q_{gd}			0.8		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 15 Ω, I_D = 1 A, V_{GEN} = 4.5 V		2		ns
Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(off)}$			12		
Fall-Time	t_f			5		

Notes

a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.